D44VH10 (NPN), D45VH10 (PNP)

Complementary Silicon Power Transistors

These complementary silicon power transistors are designed for high-speed switching applications, such as switching regulators and high frequency inverters. The devices are also well-suited for drivers for high power switching circuits.

Features

- Fast Switching
 - $t_f = 90 \text{ ns (Max)}$
- Key Parameters Specified @ 100°C
- Low Collector-Emitter Saturation Voltage -
 - $V_{CE(sat)} = 1.0 \text{ V (Max)} @ 8.0 \text{ A}$
- Complementary Pairs Simplify Circuit Designs
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Emitter Voltage	V _{CEV}	100	Vdc
Emitter Base Voltage	V _{EB}	7.0	Vdc
Collector Current - Continuous -Peak (Note 1)	I _C I _{CM}	15 20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	83 0.67	W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL CHARACTERISTICS

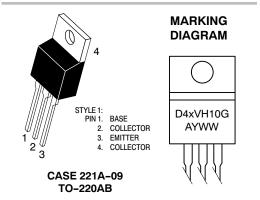
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	275	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Width \leq 6.0 ms, Duty Cycle \leq 50%.



15 A COMPLEMENTARY SILICON POWER TRANSISTORS 80 V, 83 W



x = 4 or 5

A = Assembly Location

Y = Year WW = Work Week G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping	
D44VH10	TO-220	50 Units/Rail	
D44VH10G	TO-220 (Pb-Free)	50 Units/Rail	
D45VH10	TO-220	50 Units/Rail	
D45VH10G	TO-220 (Pb-Free)	50 Units/Rail	

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

D44VH10 (NPN), D45VH10 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

	Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTI	cs					•	
Collector-Emitter Sus (I _C = 25 mAdc, I _B =	taining Voltage (Note 2) 0)		V _{CEO(sus)}	80	-	-	Vdc
Collector-Emitter Cute $(V_{CE} = Rated V_{CEV})$ $(V_{CE} = Rated V_{CEV})$			I _{CEV}		- -	10 100	μAdc
Emitter Base Cutoff C (V _{EB} = 7.0 Vdc, I _C =			I _{EBO}	-	-	10	μAdc
ON CHARACTERISTIC	S (Note 2)						
DC Current Gain (I_C = 2.0 Adc, V_{CE} = (I_C = 4.0 Adc, V_{CE}			h _{FE}	35 20		-	-
Collector-Emitter Sati ($I_C = 8.0 \text{ Adc}$, $I_B = 0$ ($I_C = 8.0 \text{ Adc}$, $I_B = 0$ ($I_C = 15 \text{ Adc}$, $I_B = 3$	0.4 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	V _{CE(sat)}	- - -	- - -	0.4 1.0 0.8 1.5	Vdc
	0.4 Adc)	D44VH10 D45VH10 D44VH10 D45VH10	V _{BE(sat)}	- - -	- - - -	1.2 1.0 1.1 1.5	Vdc
YNAMIC CHARACTE	RISTICS						
Current Gain Bandwid (I _C = 0.1 Adc, V _{CE} :	ith Product = 10 Vdc, f = 20 MHz)		f _T	-	50	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _C =	0, f _{test} = 1.0 MHz)	D44VH10 D45VH10	C _{ob}	-	120 275	-	pF
SWITCHING CHARAC	TERISTICS						
Delay Time	(V _{CC} = 20 Vdc, I _C = 8.0 Adc, I _{B1} = I _{B2} = 0.8 Adc)		t _d	1	-	50	ns
Rise Time			t _r	-	-	250	
Storage Time			t _s	-	-	700	
Fall Time			t _f	-	_	90	1

^{2.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.

D44VH10 (NPN), D45VH10 (PNP)

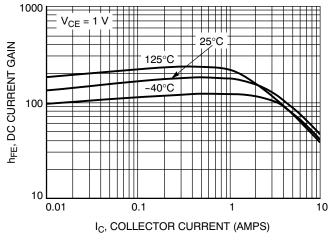


Figure 1. D44VH10 DC Current Gain

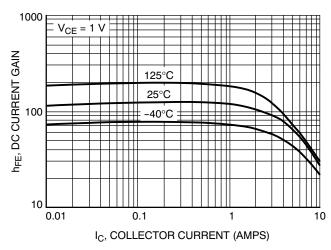


Figure 2. D45VH10 DC Current Gain

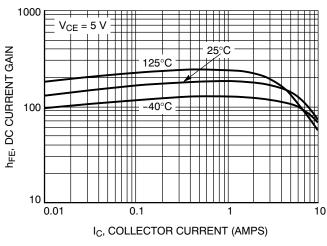


Figure 3. D44VH10 DC Current Gain

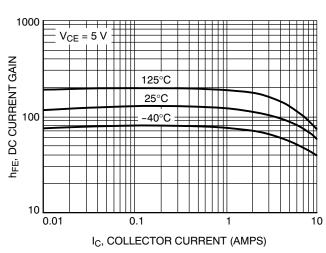


Figure 4. D45VH10 DC Current Gain

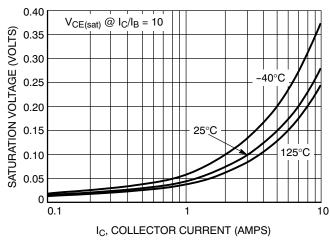


Figure 5. D44VH10 ON-Voltage

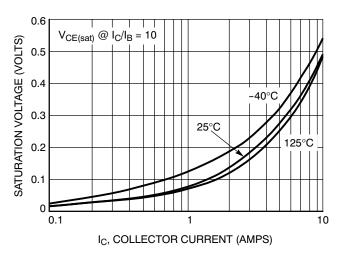


Figure 6. D45VH10 ON-Voltage